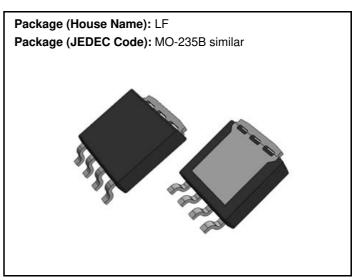
P140LF4QN

Power MOSFETs 40V, 140A, N-channel

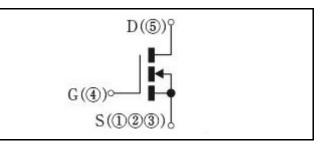
Feature

- N-channel
- Small SMD
- Large Current
- Low Ron
- 10V Gate Drive
- Low Capacitance
- Halogen free
- Pb free terminal
- RoHS:Yes

OUTLINE



Equivalent circuit



Absolute Maximum Ratings (unless otherwise specified : Tc=25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage temperature	Tstg		-55 to 175	°C
Channel tempertature	Tch		-55 to 175	°C
Drain-source voltage	V _{DSS}		40	V
Gate-source voltage	V _{GSS}		±20	V
Continuous drain current(DC)	I _D		140	Α
Continuous drain current(Peak)	I _{DP}	Pulse width 10µs, duty=1/100	560	Α
Total power dissipation	P _T		217	W
Single avalanche current	I _{AS}	Starting Tch=25°C Tch≦150°C	60	Α
Single avalanche energy	E _{AS}	Starting Tch=25°C Tch≦150°C	385	mJ

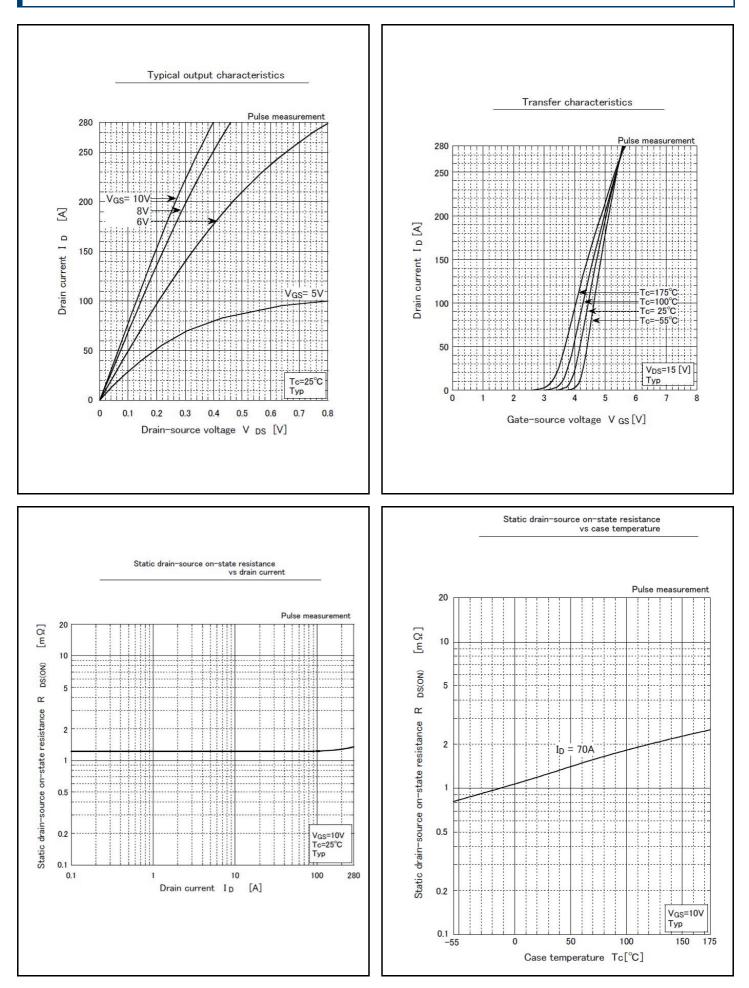
* : See the original Specifications

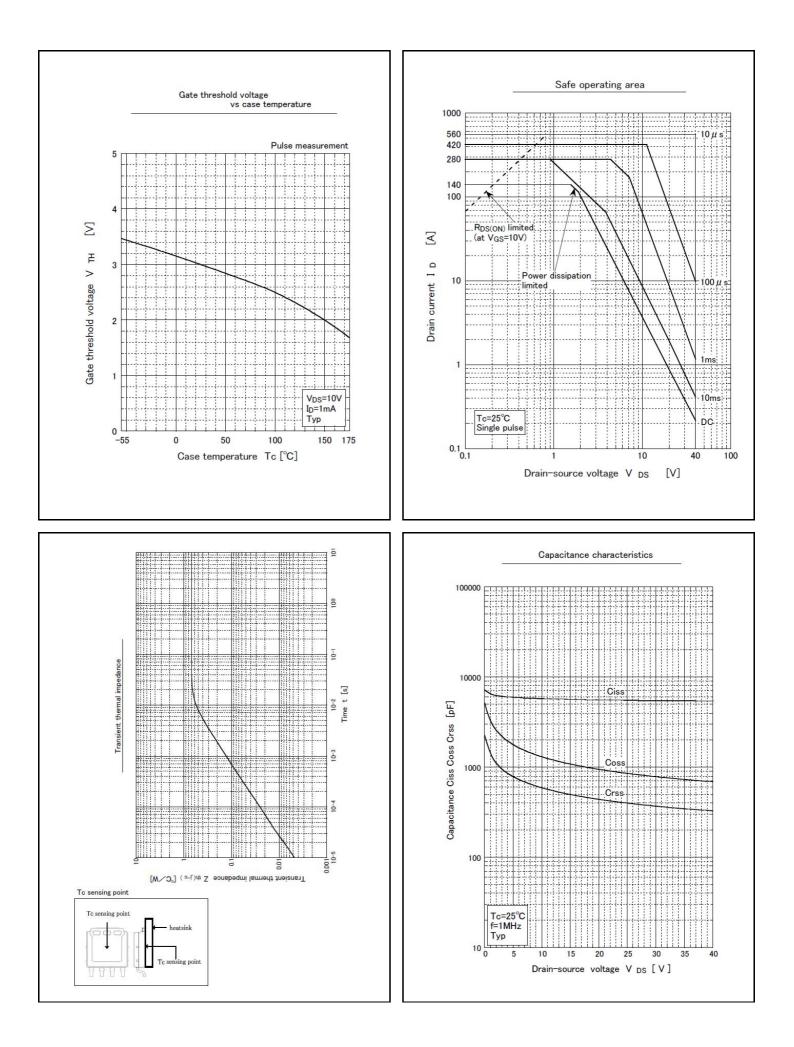
Electrical Characteristics (unless otherwise specified : Tc=25°C)

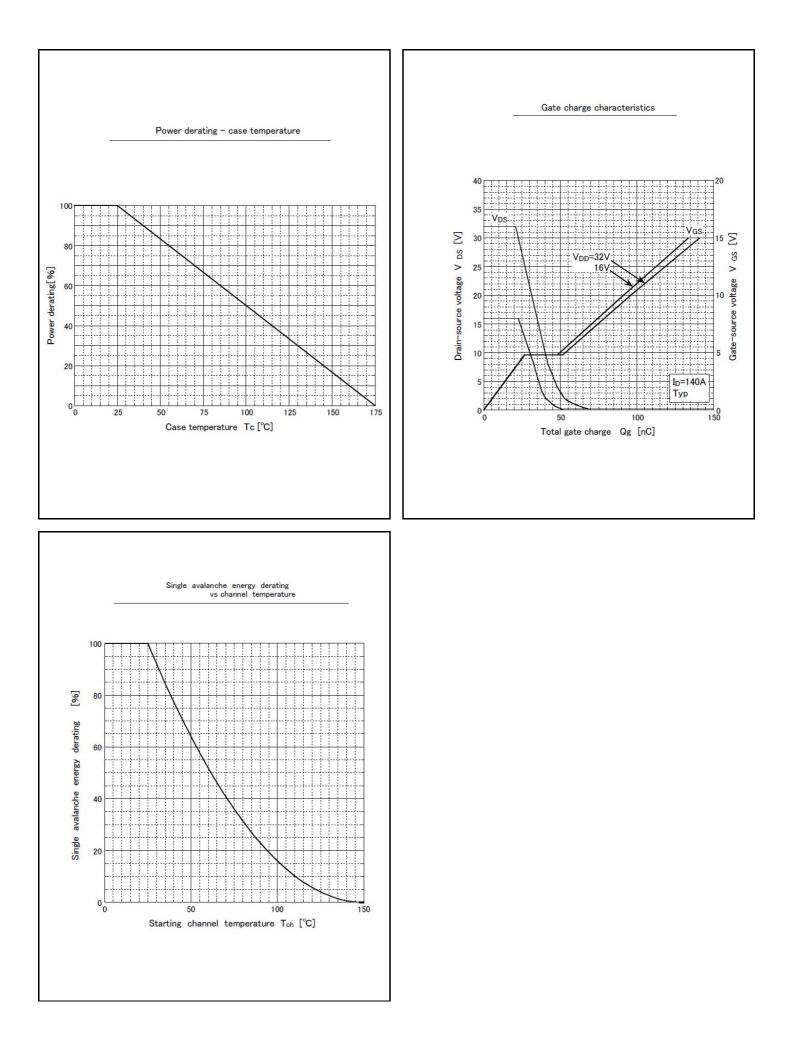
Item	Symbol	Conditions		Ratings		
			MIN	ТҮР	MAX	Unit
Drain-Source breakdown voltage	V _{(BR)DSS}	ID=1mA, VGS=0V	40			V
Zero gate voltage drain current	I _{DSS}	VDS=40V, VGS=0V			1	μA
Gate-source leakage current	I _{GSS}	VGS=±20V, VDS=0V			±0.1	μA
Forward transconductance	g fs	ID=70A, VDS=10V	20			S
Static drain-source on-state resistance	R _{DS(ON)}	ID=70A, VGS=10V		0.00122	0.00148	Ω
Gate threshold voltage	Vth	ID=1mA, VDS=10V	2	3	4	V
Source-drain diode forward voltage	V _{SD}	IS=140A, VGS=0V			1.5	V
Thermal resistance	Rth(j-c)	Junction to case, with heatsink			0.69	°C/W
Total gate charge	Qg	VDD=32V, VGS=10V, ID=140A		96		nC
Gate to source charge	Qgs	VDD=32V, VGS=10V, ID=140A		28		nC
Gate to drain charge	Qgd	VDD=32V, VGS=10V, ID=140A		39		nC
Input capacitance	Ciss	VDS=25V, VGS=0V, f=1MHz		5530		pF
Reverce transfer capacitnce	Crss	VDS=25V, VGS=0V, f=1MHz		400		pF
Output capacitance	Coss	VDS=25V, VGS=0V, f=1MHz		855		pF
Turn-on delay time	td(on)	ID=70A, RL=0.29Ω, VDD=20V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		8.5		ns
Rise time	tr	ID=70A, RL=0.29Ω, VDD=20V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		20		ns
Turn-off delay time	td(off)	ID=70A, RL=0.29Ω, VDD=20V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		80		ns
Fall time	tf	ID=70A, RL=0.29Ω, VDD=20V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		40		ns
Diode reverse recovery time	trr	IF=140A, VGS=0V, di/dt=100A/µs		44		ns
Diode reverse recovery charge	Qrr	IF=140A, VGS=0V, di/dt=100A/µs		53		nC

* : See the original Specifications

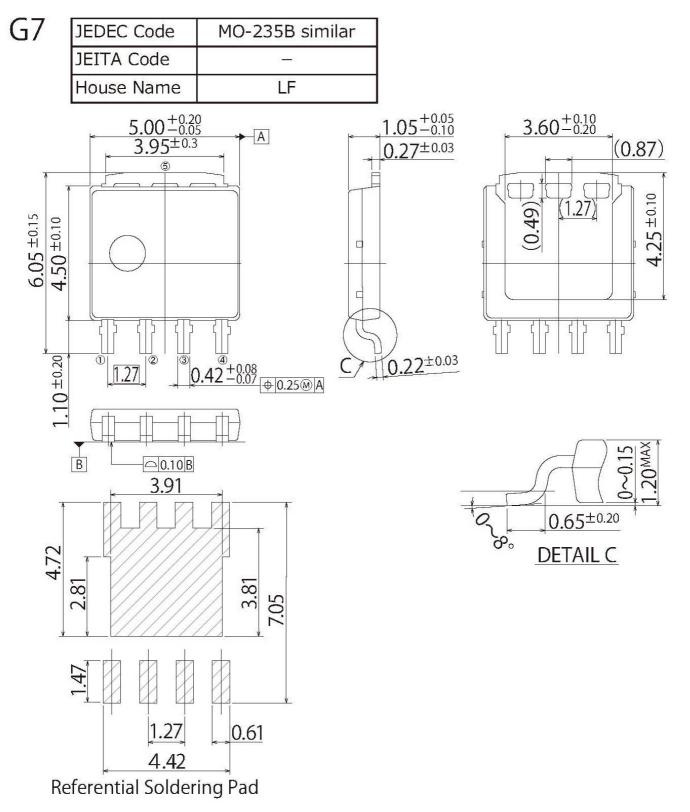
CHARACTERISTIC DIAGRAMS







unit:mm



Notes

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[Special applications]

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[Specific applications]

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